

2SC5583

Silicon NPN triple diffusion mesa type

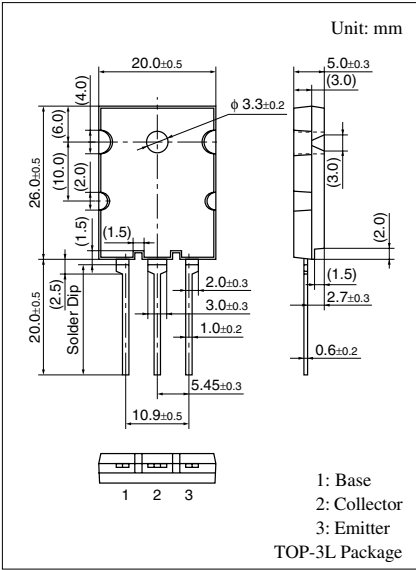
For horizontal deflection output

■ Features

- High breakdown voltage, and high reliability through the use of a glass passivation layer
- High-speed switching
- Wide area of safe operation (ASO)

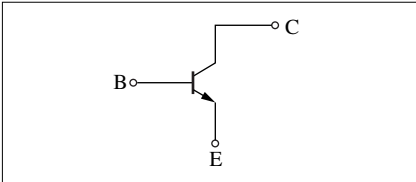
■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter		Symbol	Rating	Unit
Collector to base voltage		V_{CBO}	1 500	V
Collector to emitter voltage		V_{CES}	1 500	V
		V_{CEO}	600	V
Emitter to base voltage		V_{EBO}	7	V
Peak collector current		I_{CP}	30	A
Collector current		I_C	17	A
Base current		I_B	8	A
Collector power dissipation	$T_C = 25^{\circ}\text{C}$	P_C	150	W
	$T_a = 25^{\circ}\text{C}$		3	
Junction temperature		T_j	150	$^{\circ}\text{C}$
Storage temperature		T_{stg}	-55 to +150	$^{\circ}\text{C}$



Marking Symbol: C5583

Internal Connection



■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 1\ 000\ \text{V}, I_E = 0$			50	μA
		$V_{CB} = 1\ 500\ \text{V}, I_E = 0$			1	mA
Emitter cutoff current	I_{EBO}	$V_{EB} = 7\ \text{V}, I_C = 0$			50	μA
Forward current transfer ratio	h_{FE}	$V_{CE} = 5\ \text{V}, I_C = 8.5\ \text{A}$	6		12	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 8.5\ \text{A}, I_B = 2.13\ \text{A}$			3	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = 8.5\ \text{A}, I_B = 2.13\ \text{A}$			1.5	V
Transition frequency	f_T	$V_{CE} = 10\ \text{V}, I_C = 0.1\ \text{A}, f = 0.5\ \text{MHz}$		3		MHz
Storage time	t_{stg}	$I_C = 8.5\ \text{A}, \text{Resistance loaded}$ $I_{B1} = 2.13\ \text{A}, I_{B2} = -4.25\ \text{A}$			2.7	μs
Fall time	t_f				0.2	μs